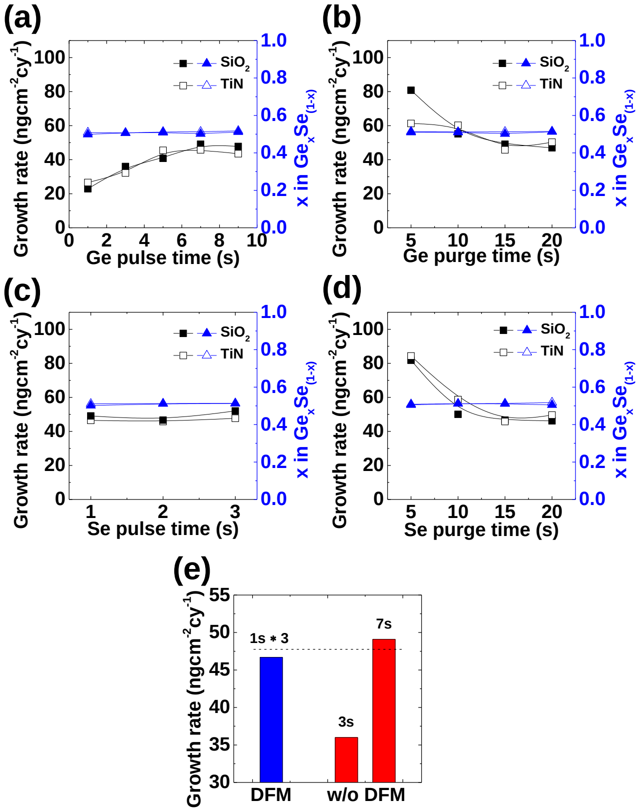

Figure 1. (a)-(d) ALD saturation growth behavior of Ge-Se deposited films at 70 ℃ (e) The comparison of saturation growth rate between ALD with DFM and without DFM process according to Ge-precursor pulse time.

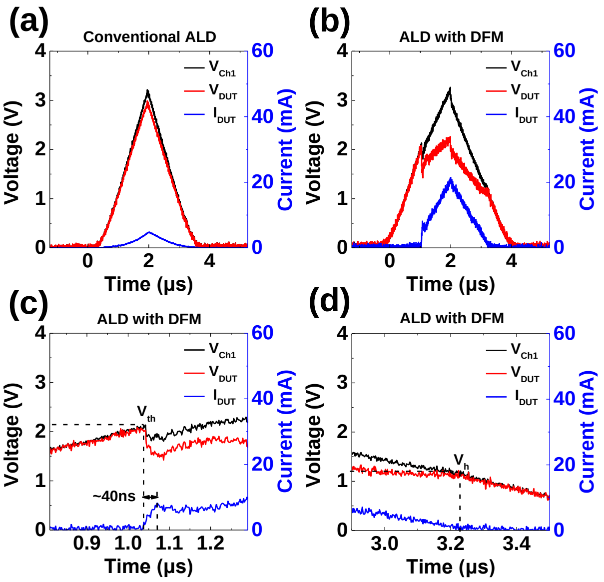

Figure 2. Time-resolved TS behavior of the GeSe selector device through (a) the conventional ALD and with (b) DFM process. Magnified view of (c) turn on and (d) turn off regions.